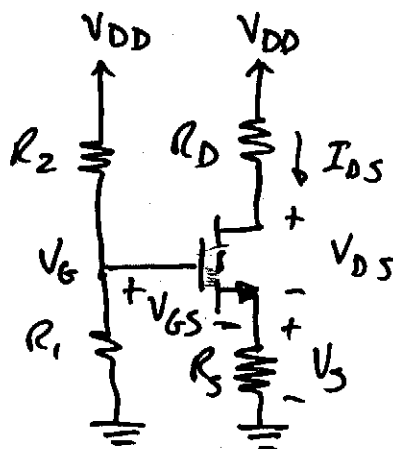


- Homework #1 - Drop problems 2 and 4 and replace with Problems 4.52 and 5.47 of the text.
- Lecture notes may be downloaded in pdf at the website - <http://users.ece.gatech.edu/~pallen/Academic/ECE3050/ece.htm>

MOS Biasing Circuits

Biasing defines the dc operating point of a diode or transistor.

- 1.) Simple biasing ckt. (Last lecture)
- 2.) More stable biasing ckt.

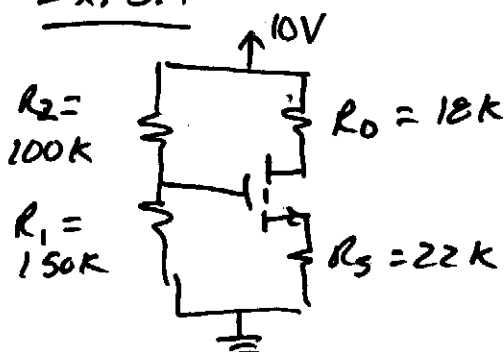


"Feedback"

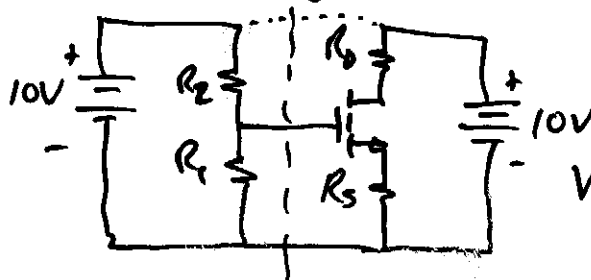
- ① Suppose I_{DS} increases.
- ② V_S increases
- ③ V_G stays constant
- ④ $\therefore V_{GS}$ decreases

$$I_{DS} = \frac{K_n' W}{2L} (V_{GS} - V_{TN})^2 \rightarrow \text{Decreases}$$

Ex. 3.1

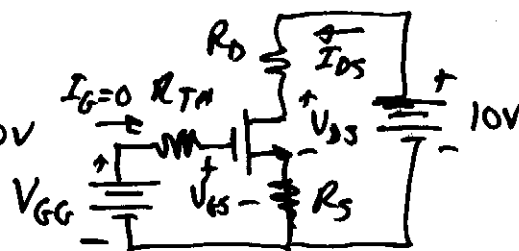


$I_G = 0$ Thev. Eq.

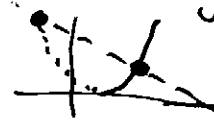


If $K_n' = 25 \mu A/V^2$, $\frac{W}{L} = 10$,
and $V_{TN} = 1V$, find Q point.
Find I_{DSQ} , V_{GSQ} , V_{DSQ}

- 1.) $V_{TH} = V_{GG} = 10 \frac{R_1}{R_1 + R_2} = 6V$
- 2.) $R_{TH} = R_1 || R_2 = 60K$



Ex. 3.1 - (cont'd)



Gate loop: $V_{GG} = V_{GS} + I_{DS} R_S$ $I_{DS} = \frac{K_N}{2} (V_{GS} - V_{TN})^2$

↑
Assume saturation

$V_{GG} = V_{GS} + \frac{R_S K_N}{2} (V_{GS} - V_{TN})^2 \rightarrow 6 = V_{GS} + 2.75 (V_{GS} - 1)^2$

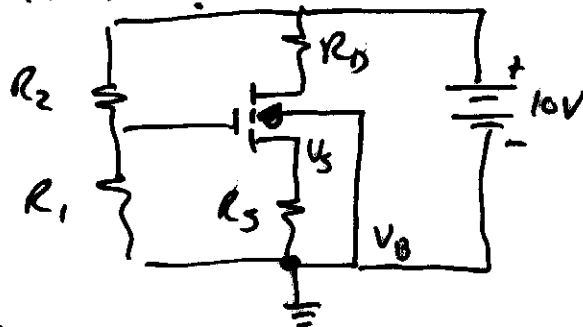
$V_{GS} = 0.8182 \pm 1.361 \rightarrow \underline{V_{GSQ} = 2.179V}$

$I_{DSQ} = \frac{25 \cdot 10}{2} (2.179 - 1)^2 \mu A = \underline{174 \mu A}$

$V_{DD} = I_{DSQ} (R_D + R_S) + V_{DSQ} \rightarrow V_{DSQ} = 10 - 174(204) = \underline{3.05V}$

Saturation occurs when $V_{DS} \geq V_{GS} - V_{TN}$

$3.05 \geq 2.179 - 1$ Yes
Bulk effect?



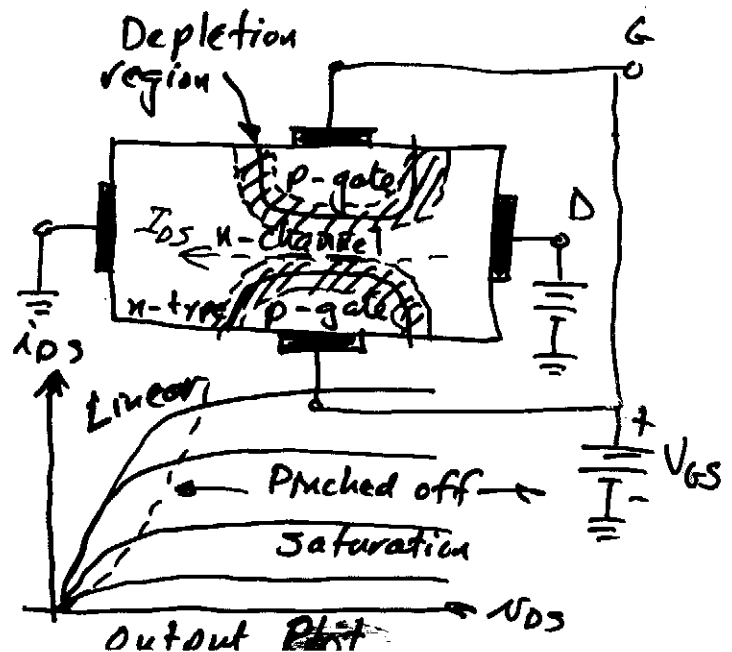
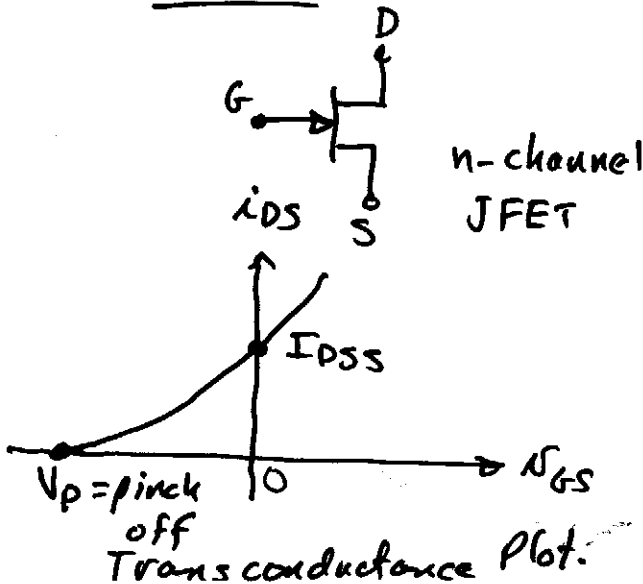
$V_{BS} = -V_S = -16K(174 \mu A)$

$V_{TN} = V_{T0} + \gamma \sqrt{2\phi_F - V_{BS}} - \gamma \sqrt{2\phi_F}$

Parameters of the MOSFET Large Signal Models are

$K_N', V_{T0}, \gamma, \lambda, 2\phi_F \rightarrow K_N' \ \& \ V_{TN}$

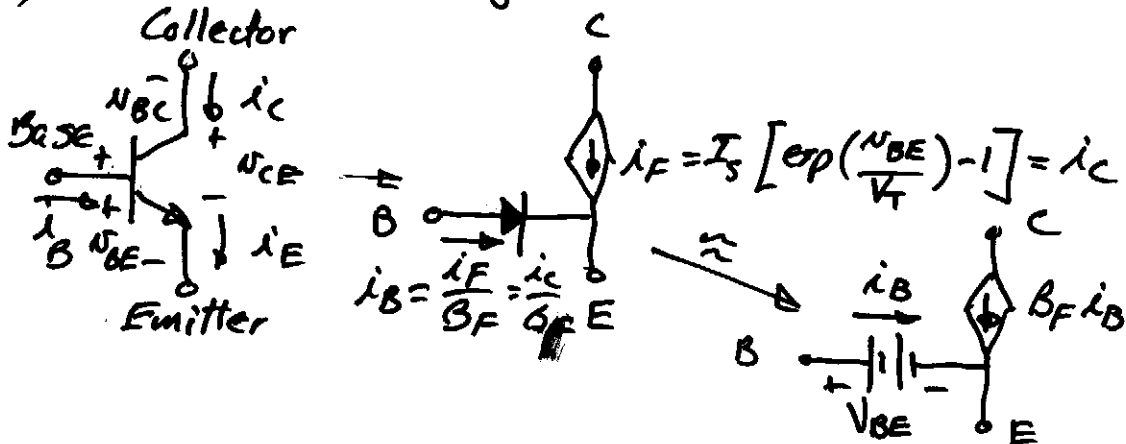
JFETs



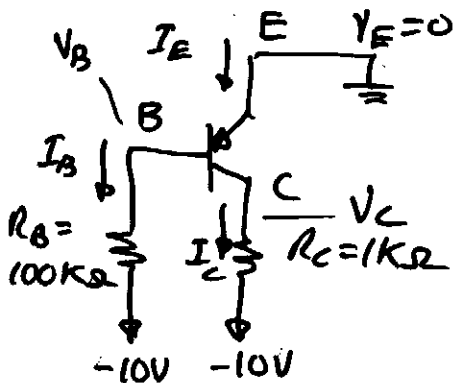
BJTs - Bipolar Junction Transistors

NPN Large Signal Model -

1.) Forward active region (BC is rev. biased, BE is fwd. biased)



2.) EX. 3.2



If $\beta_F = 50$
 And all
 dc currents and dc voltages.

Only good when i_B is mostly defined by the external circuit.

$$I_B = \frac{10 - V_{EB}}{100k} \approx \frac{10V}{100k} = 100\mu A$$

or can assume $V_{EB} \approx 0.7V$

$$\therefore I_B = \frac{10 - 0.7}{100k} = \underline{\underline{93\mu A}}$$

$$I_C = \beta_F I_B = 50 I_B = \underline{\underline{4.65\mu A}}$$

$$I_E = I_C + I_B = \underline{\underline{4.74\mu A}}$$

$$\underline{\underline{V_E = 0}} \quad \underline{\underline{V_B \approx -0.7V}} \quad \underline{\underline{V_C = -10 + I_C R_C = -5.35V}}$$

Next,

